

SILICON BIDIRECTIONAL DIACS	POWER DISSIPATION 150 mW
FEATURES - Three way layer two terminal, axial lead , hermetically sealed diacs are designed specifically for triggering thyristors .The demonstrate low breakover current. The breakover symmetry is within three volts(DB3,DB4) or four volts(DB6).These diacs are intended for use in thyristors phase control.,circuits for lamp dimming universal motor speed control and heat control - This diode is also available in the DO-35case.	DO - 35 Dimensions in inches and (millimeters)

ABSOLUTE RATINGS

PARAMETERS	SYMBOL	VALUE			UNITS
		DB3	DB4	DB6	
Power Dissipation on Printed Circuit(L=10mm) TA=50°C	Pc	150			mW
Repetitive Peak on-state Current Tp=10uS f=100Hz	ITRM	2.0			A
Storage and Operating Junction Temperature	TSTG/TJ	-44 to+125/-40 to+110			°C

ELECTRICAL CHARACTERISTICS

PAPRAMETERS	SYMBOLS	TEST CONDITIONS		VALUE			UNITS
				DB3	DB4	DB6	
Breakover Voltage*	VBo	C=22nf** See Diagram 1	Min	28	35	56	V
			Typ	32	40	60	
			Max	36	45	70	
Breakover Voltage Symmetry	1+VBo/- 1-VBo	C=22nf** See Diagram 1	Max	±3			V
Dynamic Breakover Voltage	1±ΔV1	ΔI=(IBo to IF=10mA) See FIG 1	Min	5			V
Output Voltage*	Vo	See FIG 2	Min	5			V
Breakover Current*	IBo	C=22nf**	Max	100			uA
Rise Time*	tr	See FIG 3	Typ	1.5			uS
Leakage Current*	IB	IB=0.5 VBo MAX See FIG 3	Max	10			uA

NOTE:* Electrical characteristics applicable in both forward and reverse directions.

** Connected in parallel with the devices.

FIG.1-CURRENT-VOLTAGE CHARACTERISTICS

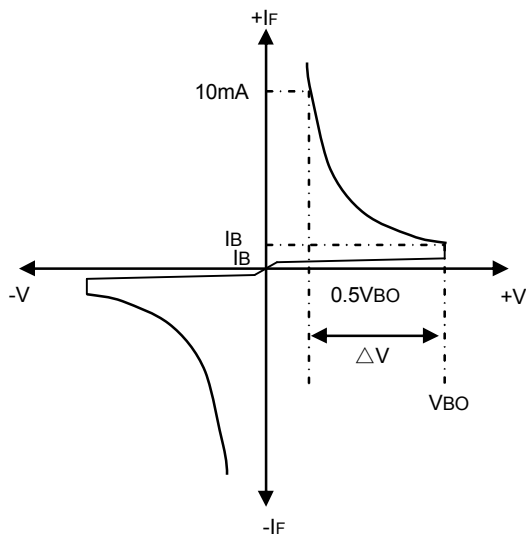


FIG.2-TEST CIRCUIT FOR OUTPUT VOLATGE

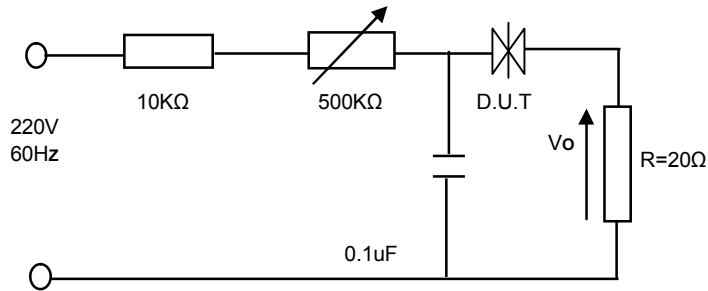


FIG.3-TEST CIRCUIT SEE FIG.2 ADJUST R
FOR $I_p=0.5\text{A}$

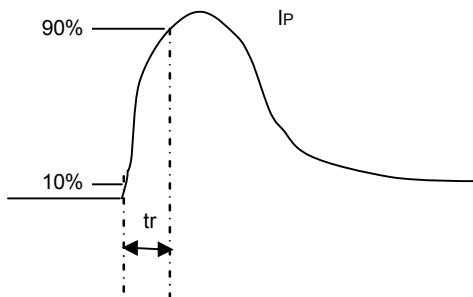


FIG.4-TEST CIRCUIT FOR OUTPUT

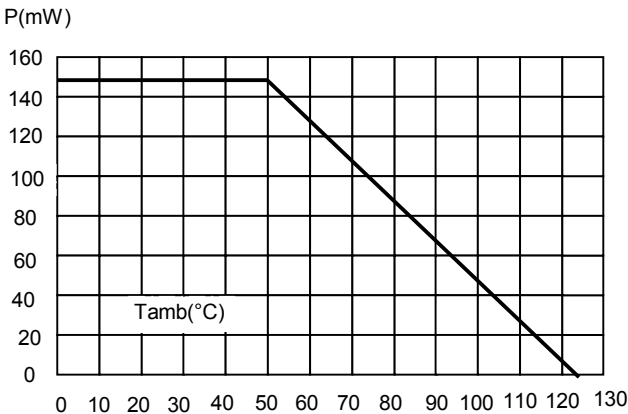


FIG.5-RELATIVE VARIATION OF V_{BO} VERSUS
JUNCTION TEMPERATURE(TYPICAL VALUES)

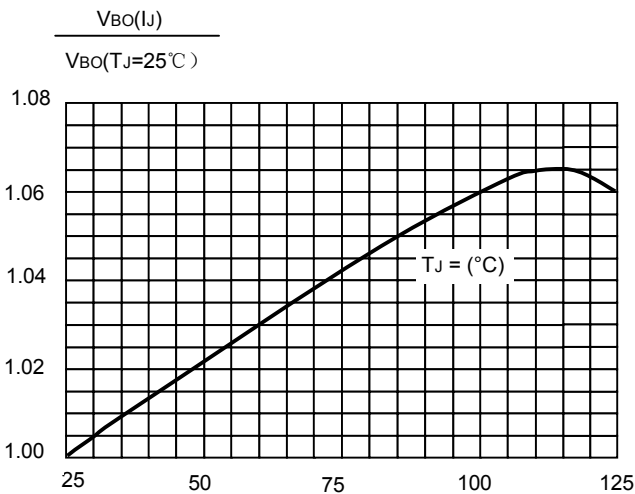


FIG.6-PEAK PULSE CURRENT VERSUS PULSE
DURATION (MAXIMUM VALUES)

